



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089

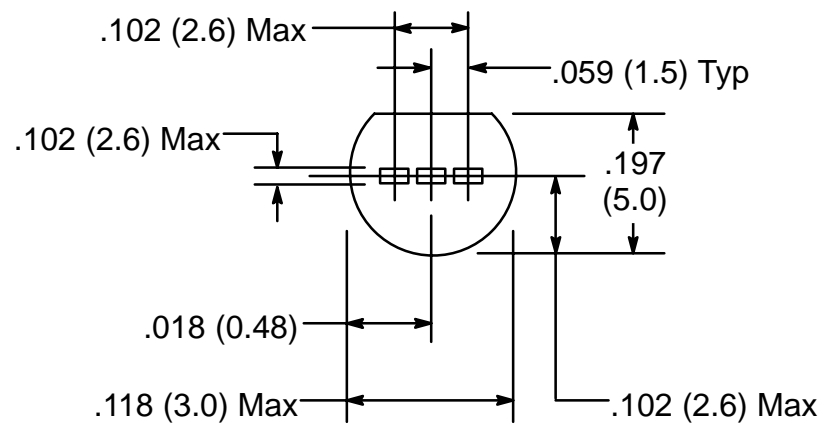
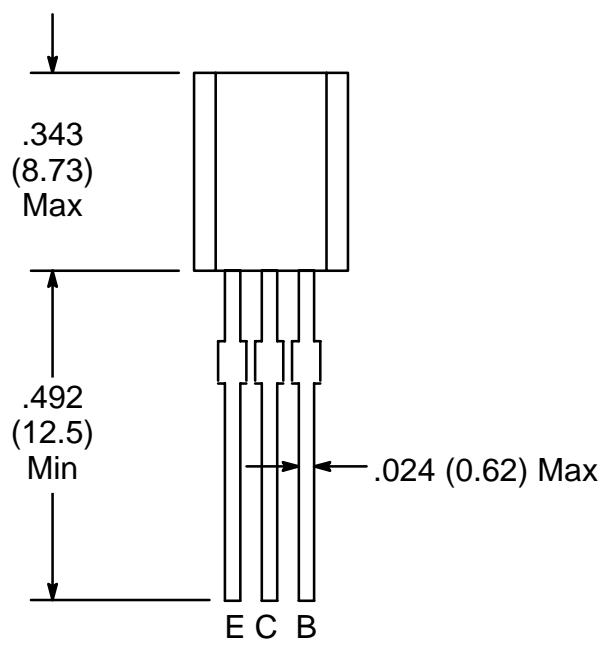
NTE382 (NPN) & NTE383 (PNP) Silicon Complementary Transistors Audio Frequency Driver

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	120V
Collector–Emitter Voltage, V_{CEO}	100V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	1A
Peak	2A
Collector Power Dissipation, P_C	900mW
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	120	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	100	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 100\text{V}, I_E = 0$	–	–	10	μA
DC Current Gain	h _{FE}	$V_{CE} = 5\text{V}, I_C = 150\text{mA}$	160	–	320	
		$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	–	–	1.0	V
Base–Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 150\text{mA}$	–	–	1.5	V
Current Gain–Bandwidth Product	f _T	$V_{CE} = 5\text{V}, I_C = 150\text{mA}$	–	140	–	MHz
Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	–	20	–	pF



.236 (6.0)Dia Max

.102 (2.6) Max